**Product data sheet** 

## 1. General description

Ultrafast diode in a TO3PF package.

## 2. Features and benefits

- Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- · Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- Half-bridge / full-bridge switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_R$	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>h</sub> $\leq$ 73 °C; square-wave; Fig. 1; Fig. 2; Fig. 3	-	-	30	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; square-wave	-	-	60	Α
I <sub>FSM</sub>	non-repetitive peak	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 4</u>	-	-	170	Α
	forward current	t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN	-	-	190	Α
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.35	1.8	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.96	-	V
Dynamic ch	naracteristics					,
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	37	65	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 25 ^{\circ}C; Fig. 7$	-	85	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	138	-	ns

# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode	mb O _ O	K — A
2	K	cathode		001aaa020
3	Α	anode	0 0	
mb	n.c.	mounting base; isolated	TO3PF	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BYV30JT-600P	TO3PF	Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack'	TO3PF		

## 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 73 °C; square-wave; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	30	Α
I <sub>O(AV)</sub>	average output current	$\delta = 0.5$ ; $T_h \le 73$ °C; SQW	-	60	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 µs; square-wave	-	60	Α
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; <u>Fig. 4</u>	-	170	Α
	forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN	-	190	Α
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

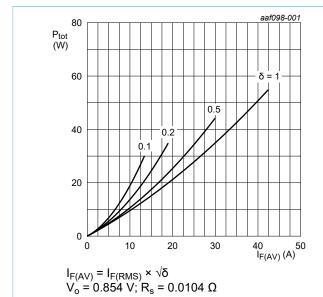


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; typical values

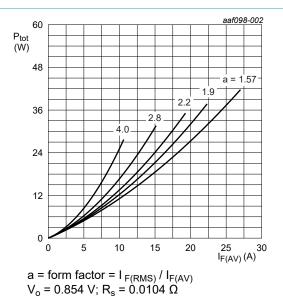
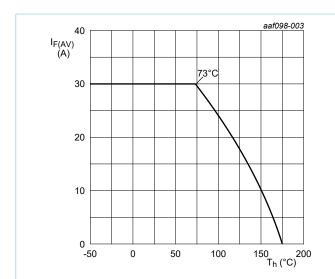


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; typical values





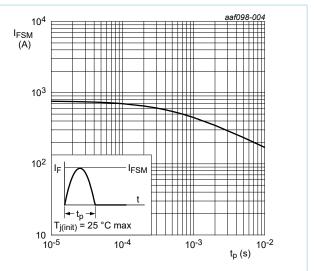


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	With heatsink compound; Fig. 5	-	2.3	2.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W

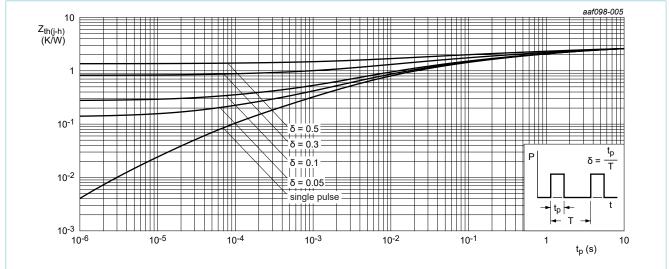
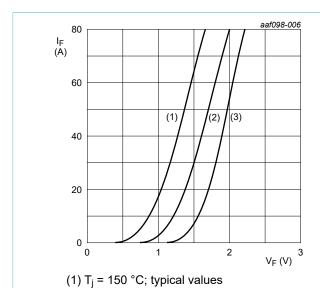


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values

## 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.35	1.8	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.96	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	500	μΑ
Dynamic ch	aracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	37	65	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	85	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	138	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}$	-	11	-	Α
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 125 ^{\circ}\text{C}$	-	18	-	Α
Q <sub>r</sub>	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	461	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_i = 125 ^{\circ}\text{C}; Fig. 7$	-	1227	-	nC



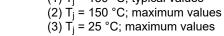


Fig. 6. Forward current as a function of forward voltage

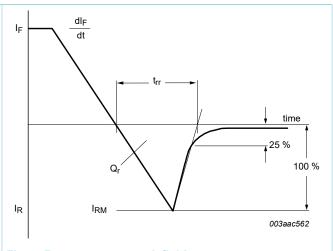
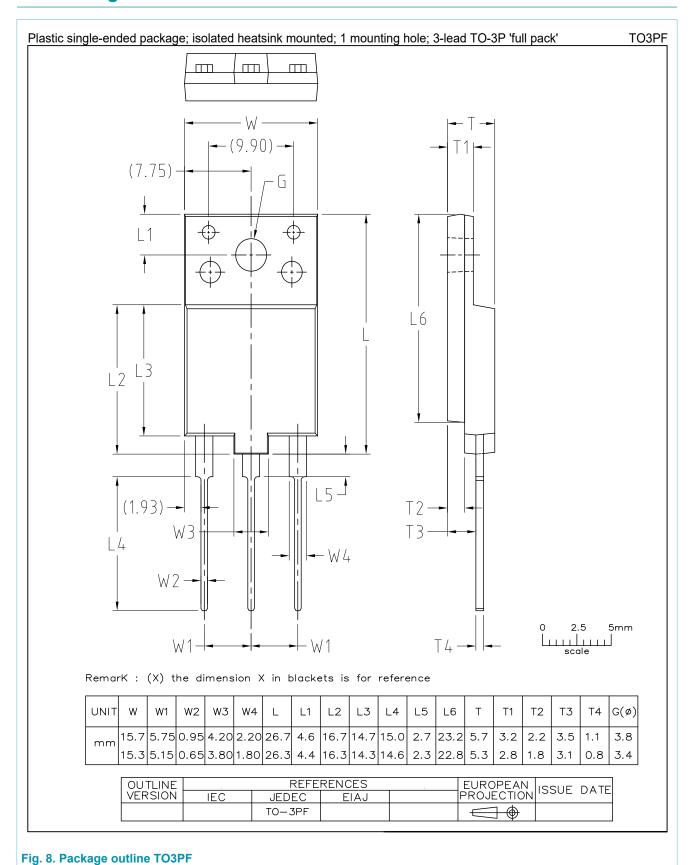


Fig. 7. Reverse recovery definitions; ramp recovery

## 10. Package outline

BYV30JT-600P



## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Ultrafast recovery diode

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